SE/EXTC/CBSGS/APM-III dt- 18/5/2017

b XTC

Q.P. Code : 13608

(3 Hours) **[Total marks : 80**

Note : -
1) Question number **1** is **compulsory.**
2) Attempt any **three** questions from the remaining **five** questions.
3) **Figures** to the **right** indicate **full** marks.

Q 1.A) Show that u = $y^3 - 3x^2y$ is a harmonic function. Also find its harmonic conjugate. **(5)**

B) Find half range Fourier sine series for f(x) = x^3, $-\pi < x < \pi$. **(5)**

C) If $\bar{F} = xye^{2z}i + xy^2coszj + x^2cosxyk$ find div$\bar{F}$ and curl$\bar{F}$ **(5)**

D) Evaluate $\int_0^\infty e^{-2t}sin^3t\ dt$. **(5)**

Q.2) A) Prove that $J_{-\frac{1}{2}}(x) = \sqrt{\frac{2}{\pi x}}\ cosx$ **(6)**

B) Find an analytic function f(z) whose imaginary part is $e^{-x}(ysiny + xcosy)$ **(6)**

C) Obtain Fourier series for f(x) = $1 + \frac{2x}{\pi}$ $-\pi \leq x \leq 0$

$= 1 - \frac{2x}{\pi}$ $0 \leq x \leq \pi$

Hence deduce that $\frac{\pi^2}{8} = \frac{1}{1^2} + \frac{1}{3^2} + \frac{1}{5^2} + \ldots$ **(8)**

Q.3) A) Show that $\bar{F} = (2xyz^2)i + (x^2z^2 + zcosyz)j + (2x^2yz + ycosyz)k$, is a conservative field. Find its scalar potential φ such that $\bar{F} = \nabla\varphi$ and hence, find the work done by $\bar{F}$ in displacing a particle from A(0,0,1) to B(1,π/4,2) along straight line AB **(6)**

B) Show that the set of functions $f_1(x) = 1, f_2(x) = x$ are orthogonal over (-1, 1). Determine the constants a and b such that the function $f_3(x) = -1 + ax + bx^2$ is orthogonal to both f_1 and f_2 on that interval **(6)**

TURN OVER

C) Find (i) $L^{-1}\left\{log\left[\frac{s^2+a^2}{\sqrt{s+b}}\right]\right\}$

(ii) $L\{(e^{-t}cost.H(t-\pi)\}$ **(8)**

Q.4) A) Prove that $\int J_5(x)\,dx = -J_4(x) - \frac{4}{x}J_3(x) - \frac{8}{x^2}J_2(x)$ **(6)**

B) Find inverse Laplace of $\frac{s}{(s^2-a^2)^2}$ using Convolution theorem. **(6)**

C) Expand $f(x) = \frac{3x^2-6x\pi+2\pi^2}{12}$ in the interval $0 \le x \le 2\pi$ as a Fourier series.

Hence, deduce that $\frac{\pi^2}{6} = \frac{1}{1^2} + \frac{1}{2^2} + \frac{1}{3^2} + \ldots$ **(8)**

Q.5) A) Using Gauss Divergence theorem, prove that $\iint_s (y^2z^2i + z^2x^2j + z^2y^2k).\bar{N}ds = \frac{\pi}{12}$

where S is the part of the sphere $x^2 + y^2 + z^2 = 1$ and above the xy-plane. **(6)**

B) Prove that $J_3(x) + 3J_0(x) + 4J_0'''(x) = 0$ **(6)**

C) Solve $(D^3-2D^2+5D)y = 0$, with y(0)= 0, y'(0)=0 and y"(0)= 1, **(8)**

Q.6) A) Evaluate by Green's theorem for $\int_c(\frac{1}{y}\,dx + \frac{1}{x}dy)$ where C is the

the boundary of the region define by x = 1, x = 4, y = 1 and $y = \sqrt{x}$ **(6)**

B) Find the bilinear transformation which maps the points z = 1, i, -1

onto points w = i, 0 –i **(6)**

C) Find Fourier cosine integral representation for $f(x) = e^{-ax}, x > 0$

Hence, show that $\int_0^\infty \frac{cos\omega s}{1+\omega^2}d\omega = \frac{\pi}{2}e^{-x}$, x≥ 0 **(8)**

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SE EXTC Sem-III (CBSGS) Sub- AE-1 DT- 12/5/2017

Q.P. Code : 545202

(3 Hours) Total Marks : 80

1. Question No.**1** is compulsory.
2. Answer any **three** from remaining questions.
3. **Figures** to the right indicate full marks.
4. Assume suitable data if required.

Q1. Attempt any four.

a Explain the effect of temperature of on VI characteristics of a PN junction diode. 05

b What are the important parameters of a JFET? How these parameters are determined graphically? 05

c What is Early effect? Explain how it affects the BJT characteristics in CB configuration. 05

d For the circuit shown in figure.1 draw the output waveform. Assume diode is ideal. 05

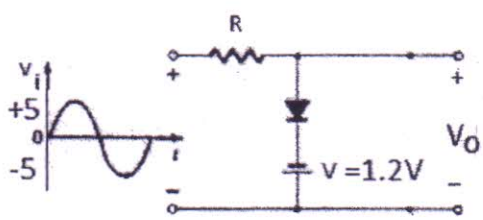

Fig.1

e For the FET shown in figure.2 the drain current equation is 05

$I_{DQ} = 9\left(1 + \frac{V_{GSQ}}{3}\right)^2$ mA, Determine I_{DQ}, V_{GSQ}, V_{DSQ}, V_D

V_{DD}=20V, R_D=2kΩ, R_S=1.5KΩ, -V_{SS}=-10V.

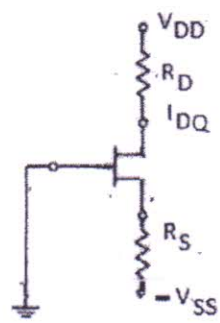

Fig .2

Q2. a Describe the construction and operation of an N-channel MOSFET in enhancement mode. Draw its characteristics and equivalent circuit of the device. 10

b Describe the different MOSFET biasing techniques .Determine the drain current, drain to source voltage, and Power dissipated in the transistor of CS circuit with an N-channel E MOSFET shown in figure 3. $R_1 = 30k\Omega$, $R_2 = 20k\Omega$, $R_D = 20k\Omega$, $R_S = 0.5k\Omega$, $V_{DD} = 5V, V_{TN} = 1V, k_N = 0.1mA/V2$ 10

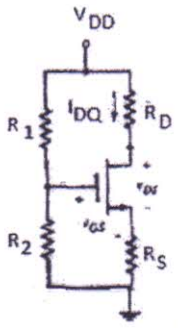

Fig.3

Q3. a Draw input and output characteristics of CE amplifier. Explain graphical analysis to determine parameters.(Zi, Zo, AV, and Ai) 10

b In the Common Emitter configuration with voltage divider bias $I_E = 1mA$ $V_{CE} = 2V$, $R_E = 1k\Omega$ and $\beta = 49$. Determine the values of R_C , R_1 and R_2 such that the stability factor does not exceed 5. Assume $V_{CC} = 5V$ and $V_{BE} = 0.3V$. 10

Q4. a For the amplifier shown in figure.4 analyze and determine 10

i) Small-signal hybrid pi parameters of BJT
ii) Small-signal voltage gain
iii) Input and output impedance.

The circuit parameters are: $R_1 = 56k\Omega$, $R_2 = 12.2k\Omega$, $R_E = 0.4k\Omega$, $R_C = 2k\Omega, R_L = 10k\Omega$, $V_{CC} = 10V$ and BJT parameters are $\beta = 100, V_{BE} = 0.7V$

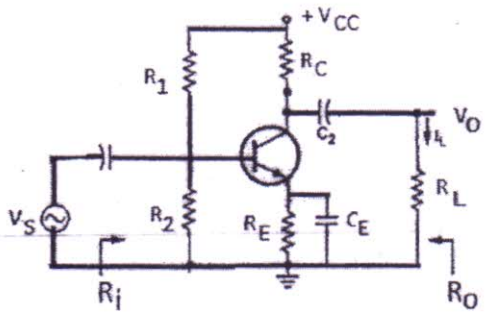

Fig.4

b Draw JFET CS amplifier with voltage divider bias and derive the expressions for the voltage gain, input impedance and output impedance. 10

Q5 a For the amplifier shown in figure.5 derive the expression for voltage gain, input and output impedance. The parameters of the MOSFET in the circuit shown in fig .5 are ; $R_G = 1M\Omega$, $V_{DD} = 5V, -V_{SS} = -5V, V_{TN} = 0.8\,V, k_N = 0.85\ \ mA/V^2$ 10

(i) Determine the values of R_S and R_D such that I_{DQ}=0.1mA and maximum symmetrical 1V peak sinusoidal signal occurs at output.(ii) Find the small signal transistor parameters. (iv) Determine the small-signal voltage gain A_V

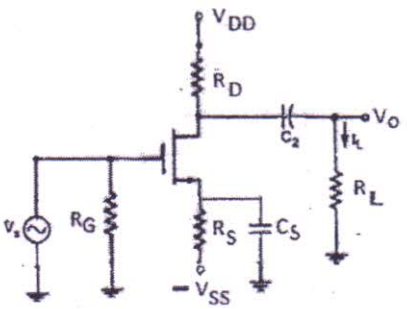

Fig.5

b Draw the circuit diagram of Wein Bridge Oscillator and derive the expression for the frequency of oscillation and minimum gain required for sustained oscillation 10

Q6 Write a short note on following 20

a Twin-T Oscillator.

b Varactor Diode (Construction and operation)

c D C load line concept in BJT. Why Q point should be at the middle of DC load line and fixed?

d MOS capacitor

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Dt - 24/5/2017

SE/EXTC/Sem-III/CBSGS

Q.P. Code : 545402

(3 Hours) **[Total Marks : 80**

N.B. : (1) **Question No. 1** is compulsory.
(2) **Attempt any 3** questions from Q.2 to Q.6.
(3) Figures to the **right** in the bracket indicate **full** marks.
(4) Assume suitable data if necessary.

1. a) Compare Combinational circuits with Sequential circuits. **5**
b) Compare Synchronous counter with Asynchronous counter. **5**
c) Compare Moore machine with Mealy machine. **5**
d) Compare SRAM with DRAM. **5**

2. a) Implement the following Boolean equation using single 4:1 MUX and few logic gates : $F(A,B,C,D) = \Sigma\, m(0, 2, 5, 6, 7, 9, 12, 15)$. **10**
b) State and prove the De Morgan's theorem. **5**
c) Implement $Y = A + \overline{BC}$ using only NOR gates. **5**

3. a) Draw a neat circuit of BCD adder using IC 7483 and explain. **10**
b) Using Quine McClusky method, minimize the following: **10**
$F(P,Q,R,S) = \Sigma$ m(0,1,2,3,5,7,8,9,11,14).

4. a) Design synchronous counter using D type flip flops for getting the following sequence: $0 \rightarrow 3 \rightarrow 1 \rightarrow 5 \rightarrow 6 \rightarrow 0$. **10**
Take care of lockout condition.
b) Convert JK type flip flop into D type flip flop. **5**
c) Write $(27)_{16}$ into its BCD code and Octal code. **5**

5. a) Write the VHDL code for 3-bit up-down counter with negative edge triggered clock and active low Preset and Clear terminals. **10**
b) Compare TTL with CMOS logic families. **5**
c) Draw the internal logic diagram of Programmable Logic Array (PLA). **5**

6. a) What is shift register? Explain any one type of shift register. Give its application. **10**
b) Design a Mealy type sequence detector circuit to detect a sequence 1011 using D type flip flops. **10**
